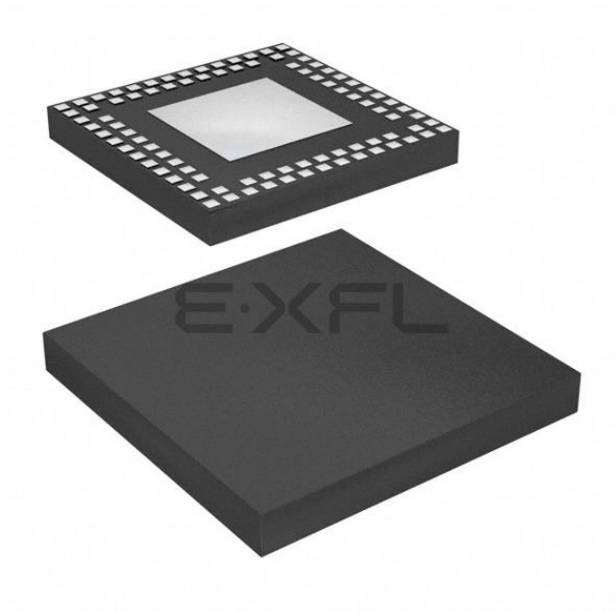

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	EBI/EMI, I²C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, POR, PWM, WDT
Number of I/O	65
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 32x12b; D/A 2x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	92-VFLGA Dual Rows, Exposed Pad
Supplier Device Package	92-LGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/sim3c167-b-gm

1. Related Documents and Conventions

1.1. Related Documents

This data sheet accompanies several documents to provide the complete description of the SiM3C1xx device family.

1.1.1. SiM3U1xx/SiM3C1xx Reference Manual

The Silicon Laboratories SiM3U1xx/SiM3C1xx Reference Manual provides detailed functional descriptions for the SiM3C1xx devices.

1.1.2. Hardware Access Layer (HAL) API Description

The Silicon Laboratories Hardware Access Layer (HAL) API provides C-language functions to modify and read each bit in the SiM3C1xx devices. This description can be found in the SiM3xxxx HAL API Reference Manual.

1.1.3. ARM Cortex-M3 Reference Manual

The ARM-specific features like the Nested Vector Interrupt Controller are described in the ARM Cortex-M3 reference documentation. The online reference manual can be found here:
http://infocenter.arm.com/help/topic/com.arm.doc.subset.cortexm.m3/index.html#cortexm3.

1.2. Conventions

The block diagrams in this document use the following formatting conventions:

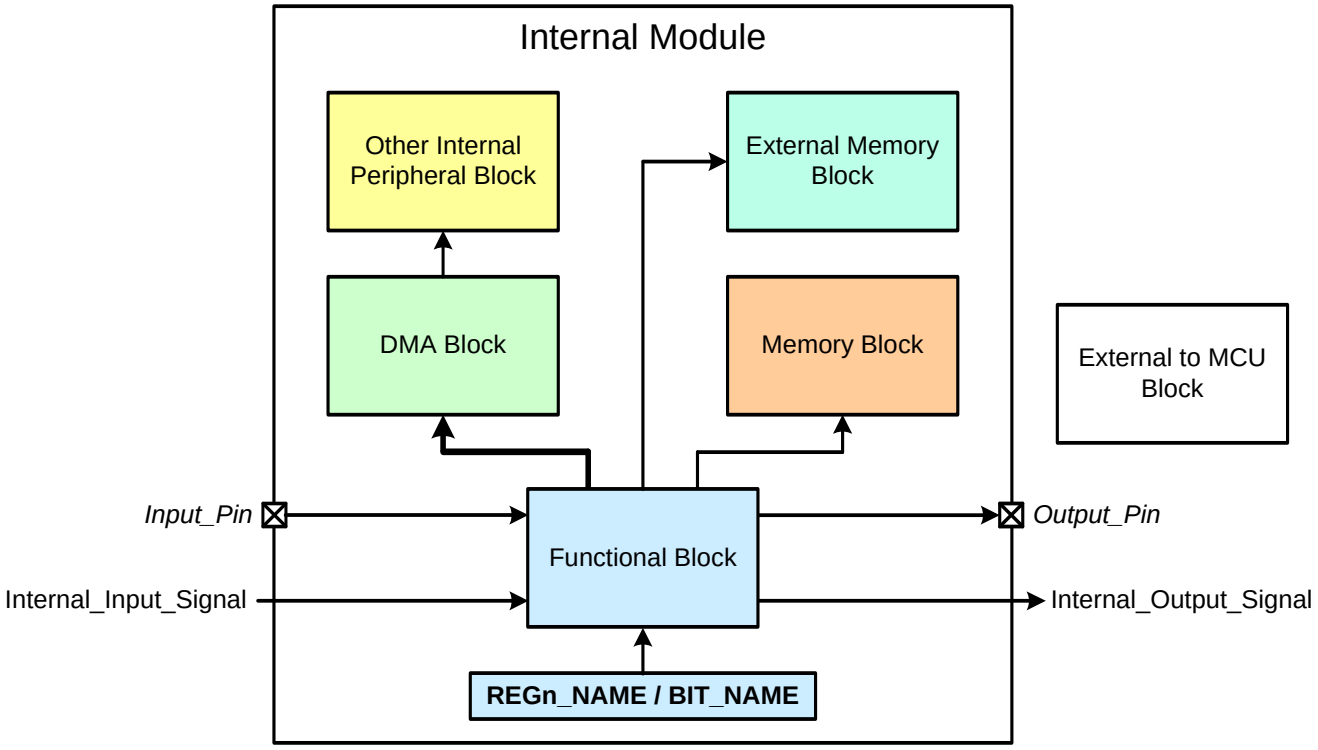


Figure 1.1. Block Diagram Conventions

Table 3.8. Internal Oscillators (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Low Power Oscillator (LPOSC0)						
Oscillator Frequency	f_{LPOSC}	Full Temperature and Supply Range	19	20	21	MHz
		T_A = 25 °C, V_{DD} = 3.3 V	19.5	20	20.5	MHz
Divided Oscillator Frequency	f_{LPOSCD}	Full Temperature and Supply Range	2.375	2.5	2.625	MHz
Power Supply Sensitivity	PSS_{LPOSC}	T_A = 25 °C	—	0.5	—	%/V
Temperature Sensitivity	TS_{LPOSC}	V_{DD} = 3.3 V	—	55	—	ppm/°C
Low Frequency Oscillator (LFOSC0)						
Oscillator Frequency	f_{LFOSC}	Full Temperature and Supply Range	13.4	16.4	19.7	kHz
		T_A = 25 °C, V_{DD} = 3.3 V	15.8	16.4	17.3	kHz
Power Supply Sensitivity	PSS_{LFOSC}	T_A = 25 °C	—	2.4	—	%/V
Temperature Sensitivity	TS_{LFOSC}	V_{DD} = 3.3 V	—	0.2	—	%/°C
RTC0 Oscillator (RTC0OSC)						
Missing Clock Detector Trigger Frequency	f_{RTCMCD}		—	8	15	kHz
RTC Robust Duty Cycle Range	DC_{RTC}		25	—	55	%
***Note:** PLL0OSC in free-running oscillator mode.						

Table 3.9. External Oscillator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
External Input CMOS Clock Frequency*	f_{CMOS}		0	—	50	MHz
External Input CMOS Clock High Time	t_{CMOSH}		9	—	—	ns
External Input CMOS Clock Low Time	t_{CMOSL}		9	—	—	ns
External Crystal Clock Frequency	f_{XTAL}		0.01	—	30	MHz
***Note:** Minimum of 10 kHz during debug operations.						

Table 3.14. Voltage Reference Electrical Characteristics

V_{DD} = 1.8 to 3.6 V, –40 to +85 °C unless otherwise specified.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Internal Fast Settling Reference						
Output Voltage	V_{REFFS}	–40 to +85 °C, V_{DD} = 1.8–3.6 V	1.62	1.65	1.68	V
Temperature Coefficient	TC_{REFFS}		—	50	—	ppm/°C
Turn-on Time	t_{REFFS}		—	—	1.5	µs
Power Supply Rejection	$PSRR_{REFFS}$		—	400	—	ppm/V
On-Chip Precision Reference (VREF0)						
Valid Supply Range	V_{DD}	VREF2X = 0	1.8	—	3.6	V
		VREF2X = 1	2.7	—	3.6	V
Output Voltage	V_{REFP}	25 °C ambient, VREF2X = 0	1.195	1.2	1.205	V
		25 °C ambient, VREF2X = 1	2.39	2.4	2.41	V
Short-Circuit Current	I_{SC}		—	—	10	mA
Temperature Coefficient	TC_{VREFP}		—	25	—	ppm/°C
Load Regulation	LR_{VREFP}	Load = 0 to 200 µA to VREFGND	—	4.5	—	ppm/µA
Load Capacitor	C_{VREFP}	Load = 0 to 200 µA to VREFGND	0.1	—	—	µF
Turn-on Time	$t_{VREFPON}$	4.7 µF tantalum, 0.1 µF ceramic bypass	—	3.8	—	ms
		0.1 µF ceramic bypass	—	200	—	µs
Power Supply Rejection	$PSRR_{VREFP}$	VREF2X = 0	—	320	—	ppm/V
		VREF2X = 1	—	560	—	ppm/V
External Reference						
Input Current	I_{EXTREF}	Sample Rate = 250 ksps; VREF = 3.0 V	—	5.25	—	µA

Table 3.15. Temperature Sensor

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Offset	V_{OFF}	T_A = 0 °C	—	760	—	mV
Offset Error*	E_{OFF}	T_A = 0 °C	—	±14	—	mV
Slope	M		—	2.8	—	mV/°C
Slope Error*	E_M		—	±120	—	µV/°C
Linearity			—	1	—	°C
Turn-on Time			—	1.8	—	µs
***Note:** Represents one standard deviation from the mean.						

Table 3.16. Comparator

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Response Time, CMPMD = 00 (Highest Speed)	t_{RESP0}	+100 mV Differential	—	100	—	ns
		–100 mV Differential	—	150	—	ns
Response Time, CMPMD = 11 (Lowest Power)	t_{RESP3}	+100 mV Differential	—	1.4	—	µs
		–100 mV Differential	—	3.5	—	µs
Positive Hysteresis Mode 0 (CPMD = 00)	HYS_{CP+}	CMPHYP = 00	—	0.4	—	mV
		CMPHYP = 01	—	8	—	mV
		CMPHYP = 10	—	16	—	mV
		CMPHYP = 11	—	33	—	mV
Negative Hysteresis Mode 0 (CPMD = 00)	HYS_{CP-}	CMPHYN = 00	—	0.4	—	mV
		CMPHYN = 01	—	–8	—	mV
		CMPHYN = 10	—	–16	—	mV
		CMPHYN = 11	—	–33	—	mV
Positive Hysteresis Mode 1 (CPMD = 01)	HYS_{CP+}	CMPHYP = 00	—	0.5	—	mV
		CMPHYP = 01	—	6	—	mV
		CMPHYP = 10	—	12	—	mV
		CMPHYP = 11	—	24	—	mV
Negative Hysteresis Mode 1 (CPMD = 01)	HYS_{CP-}	CMPHYN = 00	—	0.5	—	mV
		CMPHYN = 01	—	–6.0	—	mV
		CMPHYN = 10	—	–12	—	mV
		CMPHYN = 11	—	–24	—	mV
Positive Hysteresis Mode 2 (CPMD = 10)	HYS_{CP+}	CMPHYP = 00	—	0.6	—	mV
		CMPHYP = 01	—	4.5	—	mV
		CMPHYP = 10	—	9.5	—	mV
		CMPHYP = 11	—	19	—	mV
Negative Hysteresis Mode 2 (CPMD = 10)	HYS_{CP-}	CMPHYN = 00	—	0.6	—	mV
		CMPHYN = 01	—	–4.5	—	mV
		CMPHYN = 10	—	–9.5	—	mV
		CMPHYN = 11	—	–19	—	mV

Table 3.17. Port I/O (Continued)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
P-Channel Source Current Limit (2.7 V ≤ VIOHD ≤ 6 V, V_{OH} = VIOHD – 0.8 V) See Figure 3.2	I_{SRCL}	Mode 0	—	0.8	—	mA
		Mode 1	—	1.25	—	
		Mode 2	—	1.75	—	
		Mode 3	—	2.5	—	
		Mode 4	—	3.5	—	
		Mode 5	—	4.75	—	
		Mode 6	—	7	—	
		Mode 7	—	9.5	—	
		Mode 8	—	14	—	
		Mode 9	—	18.75	—	
		Mode 10	—	28.25	—	
		Mode 11	—	37.5	—	
		Mode 12	—	56.25	—	
		Mode 13	—	75	—	
		Mode 14	—	112.5	—	
		Mode 15	—	150	—	
Total P-Channel Source Current on P4.0-P4.5 (DC)	I_{SRCLT}		—	—	400	mA
Pin Capacitance	C_{IO}		—	30	—	pF
Weak Pull-Up Current in Low Voltage Mode	I_{PU}	V_{IOHD} = 1.8 V	–6	–3.5	–2	µA
		V_{IOHD} = 3.6 V	–30	–20	–10	µA
Weak Pull-Up Current in High Voltage Mode	I_{PU}	V_{IOHD} = 2.7 V	–15	–10	–5	µA
		V_{IOHD} = 6 V	–30	–20	–10	µA
Input Leakage (Pullups off)	I_{LK}		–1	—	1	µA

***Note:** $\overline{\text{RESET}}$ does not drive to logic high. Specifications for $\overline{\text{RESET}}$ V_{OL} adhere to the low drive setting.

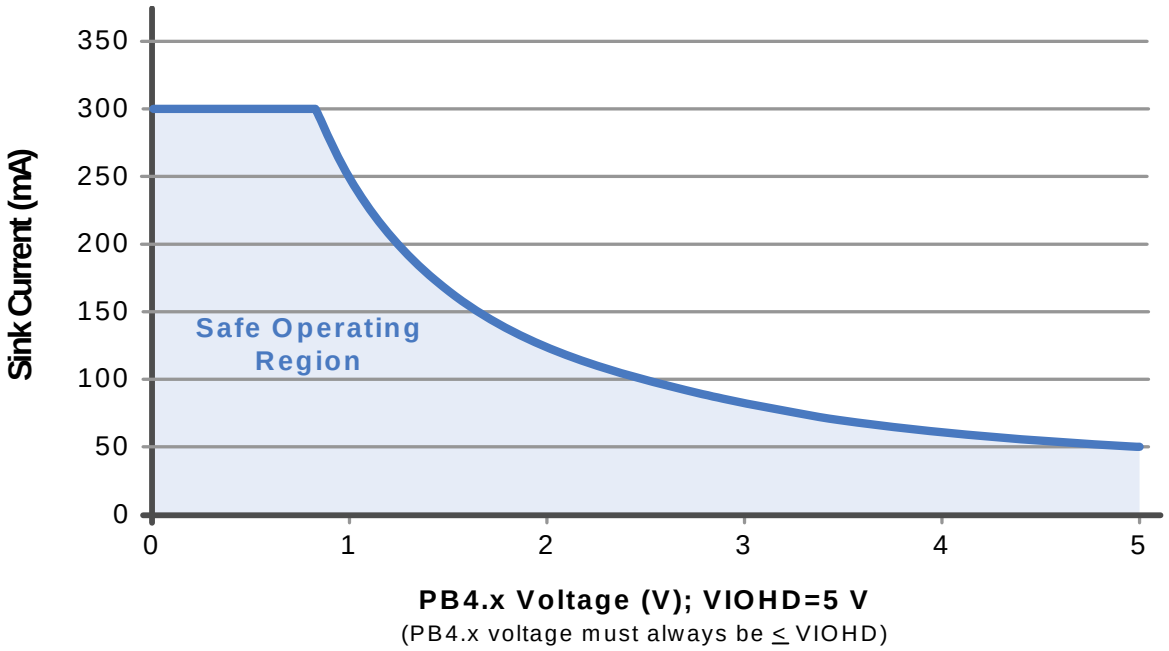


Figure 3.1. Maximum Sink Current vs. PB4.x Pin Voltage

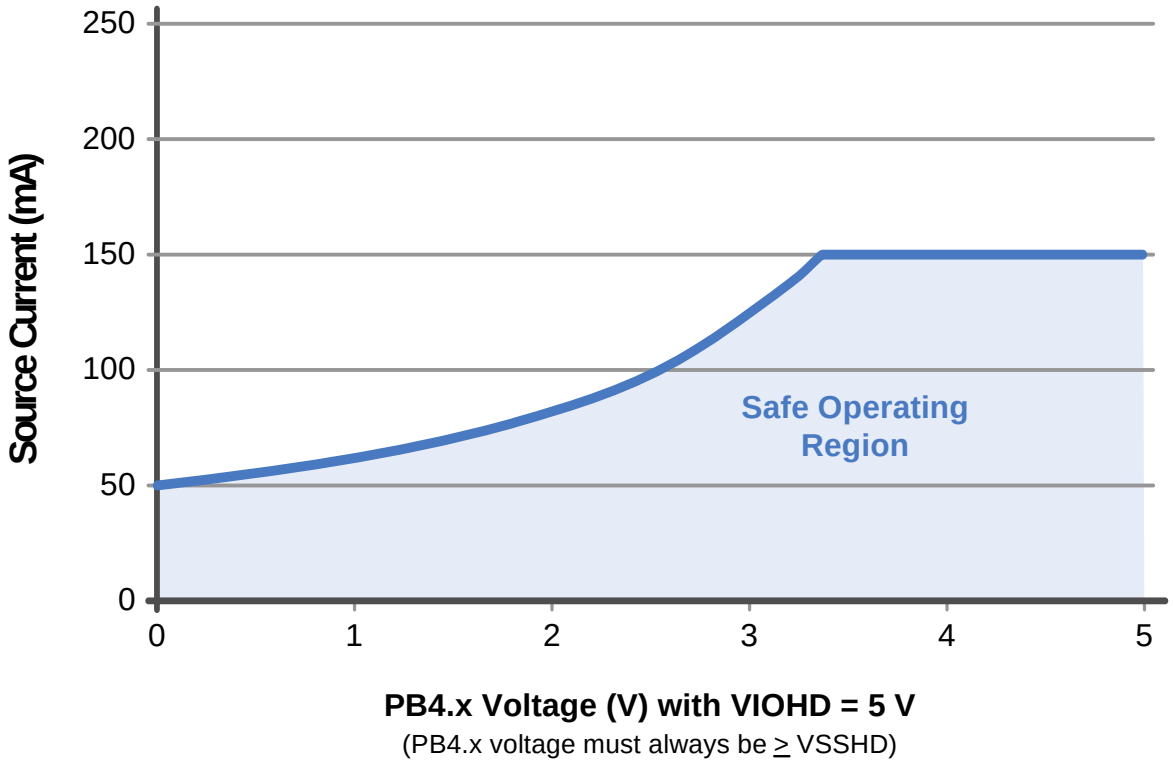


Figure 3.2. Maximum Source Current vs. PB4.x Pin Voltage

Table 3.19. Absolute Maximum Ratings (Continued)

Parameter	Symbol	Test Condition	Min	Max	Unit
Voltage on I/O pins, Port Bank 3 I/O	V_{IN}	SiM3C1x7, PB3.0–PB3.7, $V_{IO} \geq 3.3$ V	V_{SS}–0.3	5.8	V
		SiM3C1x7, PB3.0–PB3.7, $V_{IO} < 3.3$ V	V_{SS}–0.3	V_{IO}+2.5	V
		SiM3C1x7, PB3.8 - PB3.11	V_{SS}–0.3	Lowest of V_{IO}+2.5, V_{REGIN}+0.3, or 5.8	V
		SiM3C1x6, PB3.0–PB3.5, $V_{IO} \geq 3.3$ V	V_{SS}–0.3	5.8	V
		SiM3C1x6, PB3.0–PB3.5, $V_{IO} < 3.3$ V	V_{SS}–0.3	V_{IO}+2.5	V
		SiM3C1x6, PB3.6–PB3.9	V_{SS}–0.3	Lowest of V_{IO}+2.5, V_{REGIN}+0.3, or 5.8	V
		SiM3C1x4, PB3.0–PB3.3	V_{SS}–0.3	Lowest of V_{IO}+2.5, V_{REGIN}+0.3, or 5.8	V
Total Current Sunk into Supply Pins	I_{SUPP}	V_{DD}, V_{REGIN}, V_{IO}, V_{IOHD}	—	400	mA
Total Current Sourced out of Ground Pins	I_{VSS}	V_{SS}, V_{SSHD}	400	—	mA
Current Sourced or Sunk by Any I/O Pin	I_{PIO}	PB0, PB1, PB2, PB3, and $\overline{\text{RESET}}$	–100	100	mA
		PB4	–300	300	mA
Current Injected on Any I/O Pin	I_{INJ}	PB0, PB1, PB2, PB3, and $\overline{\text{RESET}}$	–100	100	mA
		PB4	–300	300	mA
Total Injected Current on I/O Pins	ΣI_{INJ}	Sum of all I/O and $\overline{\text{RESET}}$	–400	400	mA

***Note:** VSS and VSSHD provide separate return current paths for device supplies, but are not isolated. They must always be connected to the same potential on board.

4.2. I/O

4.2.1. General Features

The SiM3C1xx ports have the following features:

- Push-pull or open-drain output modes and analog or digital modes.
- Option for high or low output drive strength.
- Port Match allows the device to recognize a change on a port pin value.
- Internal pull-up resistors are enabled or disabled on a port-by-port basis.
- Two external interrupts with up to 16 inputs provide monitoring capability for external signals.
- Internal Pulse Generator Timer (PB2 only) to generate simple square waves.
- A subset of pins can also serve as inputs to the Port Mapped Level Shifters available on the High Drive Pins.

4.2.2. High Drive Pins (PB4)

The High Drive pins have the following additional features:

- Programmable safe state: high, low, or high impedance.
- Programmable drive strength and slew rates.
- Programmable hardware current limiting.
- Powered from a separate source (VIOHD, which can be up to 6 V) from the rest of the device.
- Supports various functions, including GPIO, UART1 pins, EPCA0 pins, or Port Mapped Level Shifting.

4.2.3. 5 V Tolerant Pins (PB3)

The 5 V tolerant pins can be connected to external circuitry operating at voltages above the device supply without needing extra components to shift the voltage level.

4.2.4. Crossbars

The SiM3C1xx devices have two Crossbars with the following features:

- Flexible peripheral assignment to port pins.
- Pins can be individually skipped to move peripherals as needed for design or layout considerations.

The Crossbars have a fixed priority for each I/O function and assign these functions to the port pins. When a digital resource is selected, the least-significant unassigned port pin is assigned to that resource. If a port pin is assigned, the Crossbars skip that pin when assigning the next selected resource. Additionally, the Crossbars will skip port pins whose associated bits in the PBSKIPEN registers are set. This provides some flexibility when designing a system: pins involved with sensitive analog measurements can be moved away from digital I/O and peripherals can be moved around the chip as needed to ease layout constraints.

4.4. Data Peripherals

4.4.1. 16-Channel DMA Controller

The DMA facilitates autonomous peripheral operation, allowing the core to finish tasks more quickly without spending time polling or waiting for peripherals to interrupt. This helps reduce the overall power consumption of the system, as the device can spend more time in low-power modes.

The DMA controller has the following features:

- Utilizes ARM PrimeCell uDMA architecture.
- Implements 16 channels.
- DMA crossbar supports SARADC0, SARADC1, IDAC0, IDAC1, I2C0, I2S0, SPI0, SPI1, USART0, USART1, AES0, EPCA0, external pin triggers, and timers.
- Supports primary, alternate, and scatter-gather data structures to implement various types of transfers.
- Access allowed to all AHB and APB memory space.

4.4.2. 128/192/256-bit Hardware AES Encryption (AES0)

The basic AES block cipher is implemented in hardware. The integrated hardware support for Cipher Block Chaining (CBC) and Counter (CTR) algorithms results in identical performance, memory bandwidth, and memory footprint between the most basic Electronic Codebook (ECB) algorithm and these more complex algorithms. This hardware accelerator translates to more core bandwidth available for other functions or a power savings for low-power applications.

The AES module includes the following features:

- Operates on 4-word (16-byte) blocks.
- Supports key sizes of 128, 192, and 256 bits for both encryption and decryption.
- Generates the round key for decryption operations.
- All cipher operations can be performed without any firmware intervention for a set of 4-word blocks (up to 32 kB).
- Support for various chained and stream-ciphering configurations with XOR paths on both the input and output.
- Internal 4-word FIFOs to facilitate DMA operations.
- Integrated key storage.
- Hardware acceleration for Cipher-Block Chaining (CBC) and Counter (CTR) algorithms utilizing integrated counterblock generation and previous-block caching.

4.4.3. 16/32-bit CRC (CRC0)

The CRC module is designed to provide hardware calculations for Flash memory verification and communications protocols.

The CRC module supports four common polynomials. The supported 32-bit polynomial is 0x04C11DB7 (IEEE 802.3). The three supported 16-bit polynomials are 0x1021 (CCITT-16), 0x3D65 (IEC16-MBus), and 0x8005 (ZigBee, 802.15.4, and USB).

The CRC module includes the following features:

- Support for four common polynomials (one 32-bit and three 16-bit options).
- Byte-level bit reversal for the CRC input.
- Byte-order reorientation of words for the CRC input.
- Word or half-word bit reversal of the CRC result.
- Ability to configure and seed an operation in a single register write.
- Support for single-cycle parallel (unrolled) CRC computation for 32- or 8-bit blocks.
- Capability to CRC 32 bits of data per peripheral bus (APB) clock.
- Support for DMA writes using firmware request mode.

4.6. Communications Peripherals

4.6.1. External Memory Interface (EMIF0)

The External Memory Interface (EMIF0) allows external parallel asynchronous devices, like SRAMs and LCD controllers, to appear as part of the system memory map. The EMIF0 module includes the following features:

- Provides a memory mapped view of multiple external devices.
- Support for byte, half-word and word accesses regardless of external device data-width.
- Error indicator for certain invalid transfers.
- Minimum external timing allows for 3 clocks per write or 4 clocks per read.
- Output bus can be shared between non-muxed and muxed devices.
- Available extended address output allows for up to 24-bit address with 8-bit parallel devices.
- Support for 8-bit and 16-bit (muxed-mode only) devices with up to two chip-select signals.
- Support for internally muxed devices with dynamic address shifting.
- Fully programmable control signal waveforms.

4.6.2. USART (USART0, USART1)

The USART uses two signals (TX and RX) and a predetermined fixed baud rate to communicate with a single device. In addition to these signals, the USART0 module can optionally use a clock (UCLK) or hardware handshaking (RTS and CTS).

The USART module provides the following features:

- Independent transmitter and receiver configurations with separate 16-bit baud rate generators.
- Synchronous or asynchronous transmissions and receptions.
- Clock master or slave operation with programmable polarity and edge controls.
- Up to 5 Mbaud (synchronous or asynchronous, TX or RX, and master or slave) or 1 Mbaud Smartcard (TX or RX).
- Individual enables for generated clocks during start, stop, and idle states.
- Internal transmit and receive FIFOs with flush capability and support for byte, half-word, and word reads and writes.
- Data bit lengths from 5 to 9 bits.
- Programmable inter-packet transmit delays.
- Auto-baud detection with support for the LIN SYNC byte.
- Automatic parity generation (with enable).
- Automatic start and stop generation (with separate enables).
- Transmit and receive hardware flow-control.
- Independent inversion correction for TX, RX, RTS, and CTS signals.
- IrDA modulation and demodulation with programmable pulse widths.
- Smartcard ACK/NACK support.
- Parity error, frame error, overrun, and underrun detection.
- Multi-master and half-duplex support.
- Multiple loop-back modes supported.
- Multi-processor communications support.

4.6.3. UART (UART0, UART1)

The USART uses two signals (TX and RX) and a predetermined fixed baud rate to communicate with a single device.

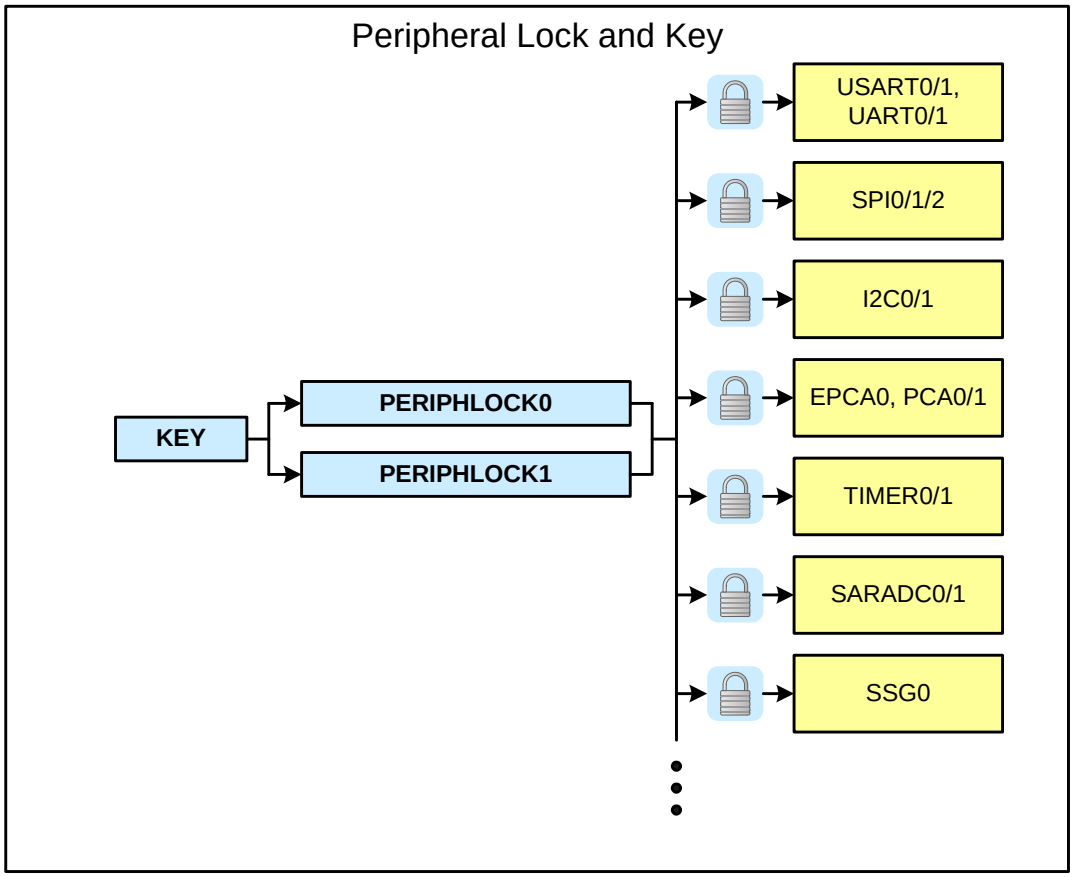
The UART module provides the following features:

- Independent transmitter and receiver configurations with separate 16-bit baud-rate generators.
- Asynchronous transmissions and receptions.
- Up to 5 Mbaud (TX or RX) or 1 Mbaud Smartcard (TX or RX).

4.9. Security

The peripherals on the SiM3C1xx devices have a register lock and key mechanism that prevents any undesired accesses of the peripherals from firmware. Each bit in the PERIPHLOCKx registers controls a set of peripherals. A key sequence must be written in order to the KEY register to modify any of the bits in PERIPHLOCKx. Any subsequent write to KEY will then inhibit any accesses of PERIPHLOCKx until it is unlocked again through KEY. Reading the KEY register indicates the current status of the PERIPHLOCKx lock state.

If a peripheral's registers are locked, all writes will be ignored. The registers can always be read, regardless of the peripheral's lock state.



4.10. On-Chip Debugging

The SiM3C1xx devices include JTAG and Serial Wire programming and debugging interfaces and ETM for instruction trace. The JTAG interface is supported on SiM3C1x7 and SiM3C1x6 devices only, and does not include boundary scan capabiites. The ETM interface is supported on SiM3C1x7 devices. The JTAG and ETM interfaces can be optionally enabled to provide more visibility while debugging at the cost of using several Port I/O pins. Additionally, if the core is configured for Serial Wire (SW) mode and not JTAG, then the Serial Wire Viewer (SWV) is available to provide a single pin to send out TPIU messages on SiM3C1x7 and SiM3C1x6 devices.

Most peripherals have the option to halt or continue functioning when the core halts in debug mode.

5. Ordering Information

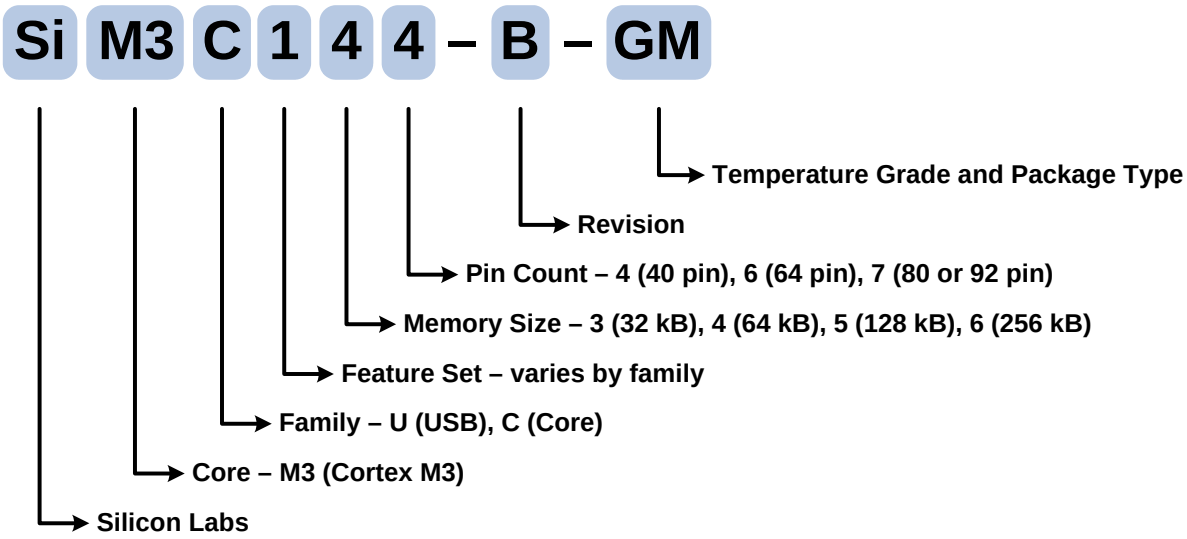


Figure 5.1. SiM3C1xx Part Numbering

All devices in the SiM3C1xx family have the following features:

- **Core:** ARM Cortex-M3 with maximum operating frequency of 80 MHz.
- **Flash Program Memory:** 32-256 kB, in-system programmable.
- **RAM:** 8–32 kB SRAM, with 4 kB retention SRAM
- **I/O:** Up to 65 multifunction I/O pins, including high-drive and 5 V-tolerant pins.
- **Clock Sources:** Internal and external oscillator options.
- **16-Channel DMA Controller.**
- **128/192/256-bit AES.**
- **16/32-bit CRC.**
- **Timers:** 2 x 32-bit (4 x 16-bit).
- **Real-Time Clock.**
- **Low-Power Timer.**
- **PCA:** 1 x 6 channels (Enhanced), 2 x 2 channels (Standard). PWM, capture, and clock generation capabilites.
- **ADC:** 2 x 12-bit 250 ksps (10-bit 1 Msps) SAR.
- **DAC:** 2 x 10-bit IDAC.
- **Temperature Sensor.**
- **Internal VREF.**
- **16-channel Capacitive Sensing (CAPSENSE).**
- **Comparator:** 2 x low current.
- **Current to Voltage Converter (IVC).**
- **Serial Buses:** 2 x USART, 2 x UART, 3 x SPI, 2 x I2C, 1 x I^2S.

The inclusion of some features varies across different members of the device family. The differences are detailed in Table 5.1.

Table 6.1. Pin Definitions and alternate functions for SiM3C1x7

Pin Name	Type	Pin Numbers TQFP-80	Pin Numbers LGA-92	Crossbar Capability (see Port Config Section)	Port Match	External Memory Interface (m = muxed mode)	Port-Mapped Level Shifter	Output Toggle Logic	External Trigger Inputs	Analog or Additional Functions
VSS	Ground	33 75	B15 B34							
VDD	Power (Core)	74	A44							
VIO	Power (I/O)	32 49 73	A19 A29 A43							
VREGIN	Power (Regulator)	76	A45							
VSSHD	Ground (High Drive)	4	B2							
VIOHD	Power (High Drive)	5	A3							
$\overline{\text{RESET}}$	Active-low Reset	80	A48							
SWCLK/TCK	Serial Wire/JTAG	45	B20							
SWDIO/TMS	Serial Wire/JTAG	44	A27							
PB0.0	Standard I/O	72	B33	XBR0	✓					ADC0.0
PB0.1	Standard I/O	71	B32	XBR0	✓					ADC0.1 CS0.0
PB0.2	Standard I/O	70	A42	XBR0	✓					ADC0.2 CS0.1
PB0.3	Standard I/O	69	B31	XBR0	✓					ADC0.3 CS0.2
PB0.4	Standard I/O	68	A41	XBR0	✓					ADC0.4 CS0.3
PB0.5	Standard I/O	67	B30	XBR0	✓					ADC0.5 CS0.4
PB0.6	Standard I/O	66	A40	XBR0	✓					CS0.5
PB0.7	Standard I/O	65	B29	XBR0	✓					ADC0.6 CS0.6 IVC0.0

6.3. SiM3C1x4 Pin Definitions

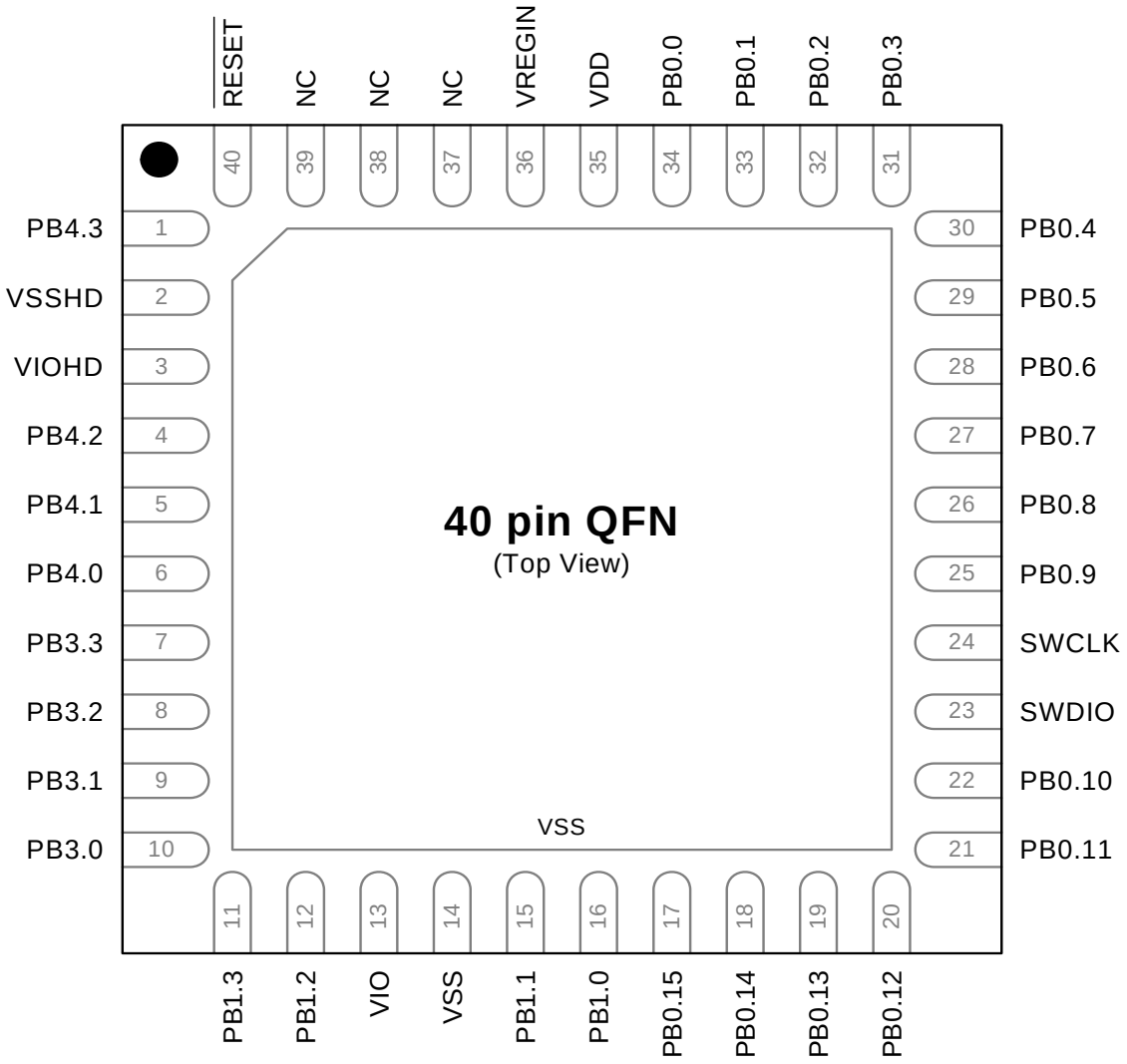


Figure 6.5. SiM3C1x4-GM Pinout

Table 6.3. Pin Definitions and Alternate Functions for SiM3C1x4 (Continued)

Pin Name	Type	Pin Numbers	Crossbar Capability (see Port Config Section)	Port Match	Output Toggle Logic	External Trigger Inputs	Analog or Additional Functions
PB0.8	Standard I/O	26	XBR0	✓			ADC0.14 ADC1.14
PB0.9	Standard I/O	25	XBR0	✓			ADC0.15 ADC1.15
PB0.10	Standard I/O	22	XBR0	✓		DMA0T1	ADC1.8
PB0.11	Standard I/O	21	XBR0	✓		DMA0T0	ADC1.7
PB0.12	Standard I/O	20	XBR0	✓		ADC0T15 WAKE.0	ADC1.5 CS0.10
PB0.13	Standard I/O	19	XBR0	✓		ADC1T15 WAKE.1	ADC1.4 CS0.11
PB0.14	Standard I/O	18	XBR0	✓		WAKE.2	ADC1.3 CS0.12
PB0.15	Standard I/O	17	XBR0	✓		WAKE.3	ADC1.2 CS0.13
PB1.0	Standard I/O	16	XBR0	✓		WAKE.4	ADC1.1 CS0.14
PB1.1	Standard I/O	15	XBR0	✓		WAKE.5	ADC1.0 CS0.15 PMU_Asleep
PB1.2	Standard I/O	12	XBR0	✓			CMP0N.0 CMP1N.0 RTC0TCLK_OUT
PB1.3	Standard I/O	11	XBR0	✓			CMP0P.0 CMP1P.0
PB3.0	5 V Tolerant I/O	10	XBR1	✓		DAC0T0 DAC1T0 LPT0T0 INT0.0 INT1.0 WAKE.12	CMP0P.1 CMP1P.1 EXREGSP

6.4.1. LGA-92 Solder Mask Design

All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.

6.4.2. LGA-92 Stencil Design

1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
2. The stencil thickness should be 0.125 mm (5 mils).
3. The ratio of stencil aperture to land pad size should be 1:1 for all perimeter pins.
4. A 2 x 2 array of 1.25 mm square openings on 1.60 mm pitch should be used for the center ground pad.

6.4.3. LGA-92 Card Assembly

1. A No-Clean, Type-3 solder paste is recommended.
2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

6.6. QFN-64 Package Specifications

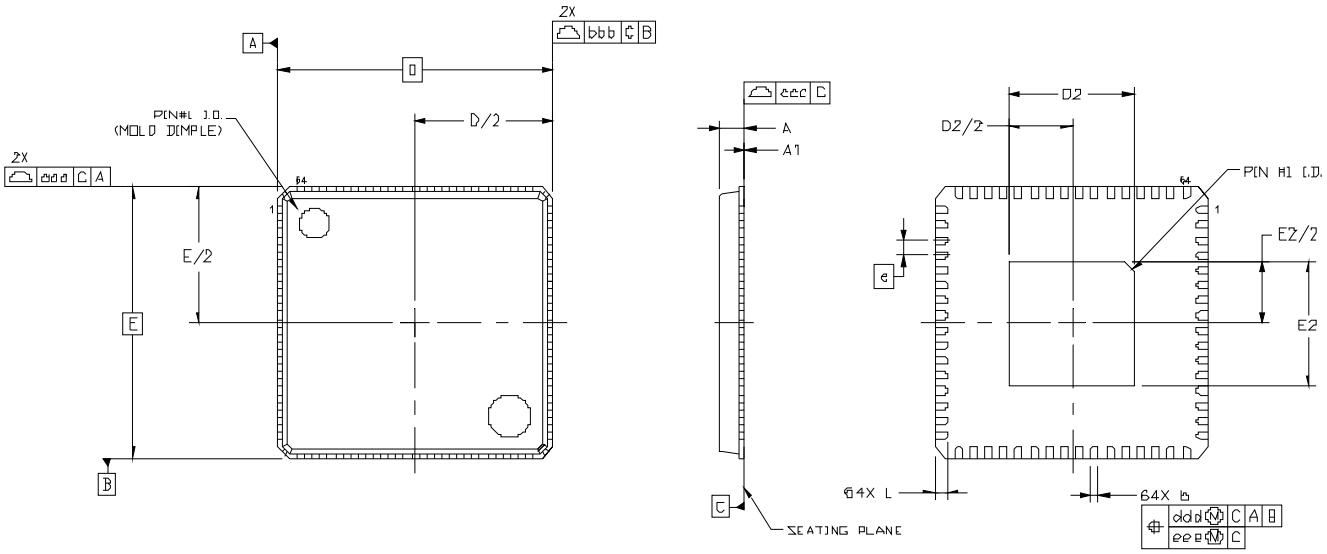


Figure 6.10. QFN-64 Package Drawing

Table 6.8. QFN-64 Package Dimensions

Dimension	Min	Nominal	Max
A	0.80	0.85	0.90
A1	0.00	0.02	0.05
b	0.18	0.25	0.30
D		9.00 BSC	
D2	3.95	4.10	4.25
e		0.50 BSC	
E		9.00 BSC	
E2	3.95	4.10	4.25
L	0.30	0.40	0.50
aaa		0.10	
bbb		0.10	
ccc		0.08	
ddd		0.10	
eee		0.05	

Notes:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. This package outline conforms to JEDEC MO-220.
4. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

6.7.1. TQFP-64 Solder Mask Design

All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.

6.7.2. TQFP-64 Stencil Design

1. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
2. The stencil thickness should be 0.125 mm (5 mils).
3. The ratio of stencil aperture to land pad size should be 1:1 for all pads.

6.7.3. TQFP-64 Card Assembly

1. A No-Clean, Type-3 solder paste is recommended.
2. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.